



## Correction: Efficiency improvement by using metal–insulator–semiconductor structure in InGaN/GaN micro-light-emitting diodes

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**Correction:** *Front. Optoelectron.* 17, 8 (2024)  
<https://doi.org/10.1007/s12200-024-00111-9>

Following publication of the original article [1], the authors reported errors in the legend of Graphical Abstract, Figure 2 and Figure 3.

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The original article can be found online at <https://doi.org/10.1007/s12200-024-00111-9>.

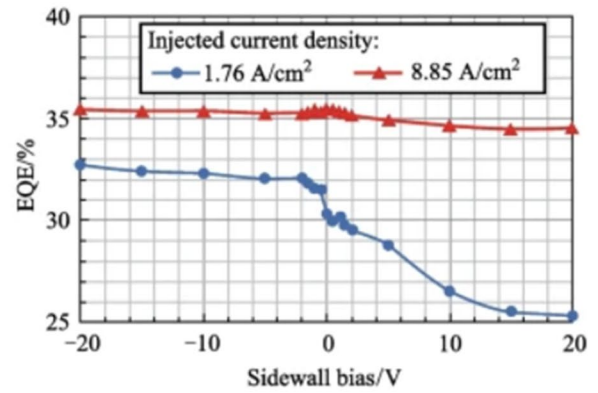
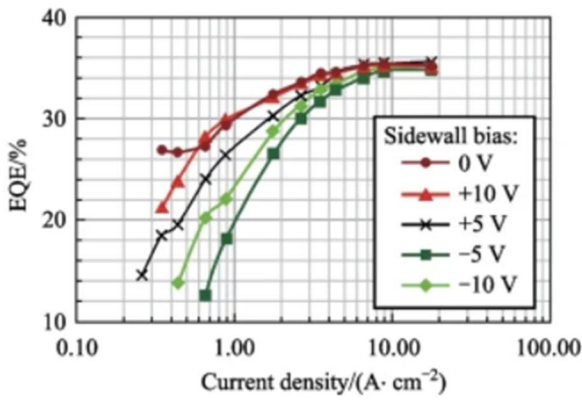
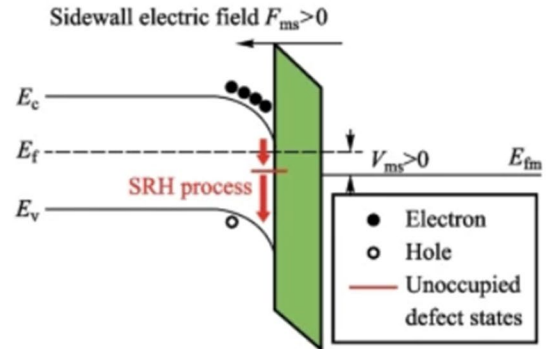
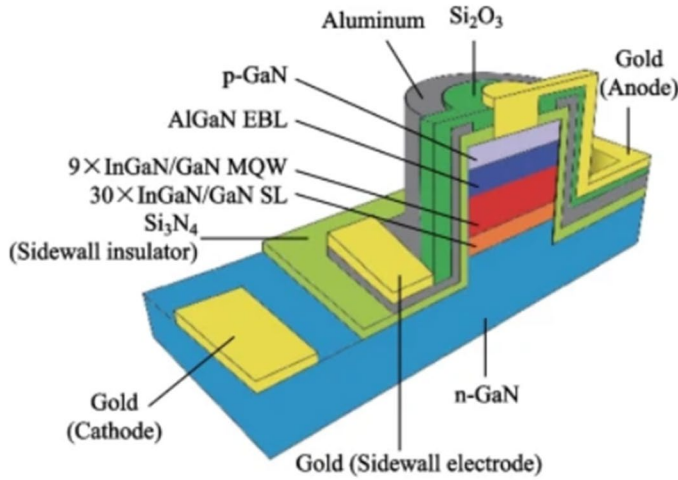
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The Graphical Abstract has been updated from:



To:

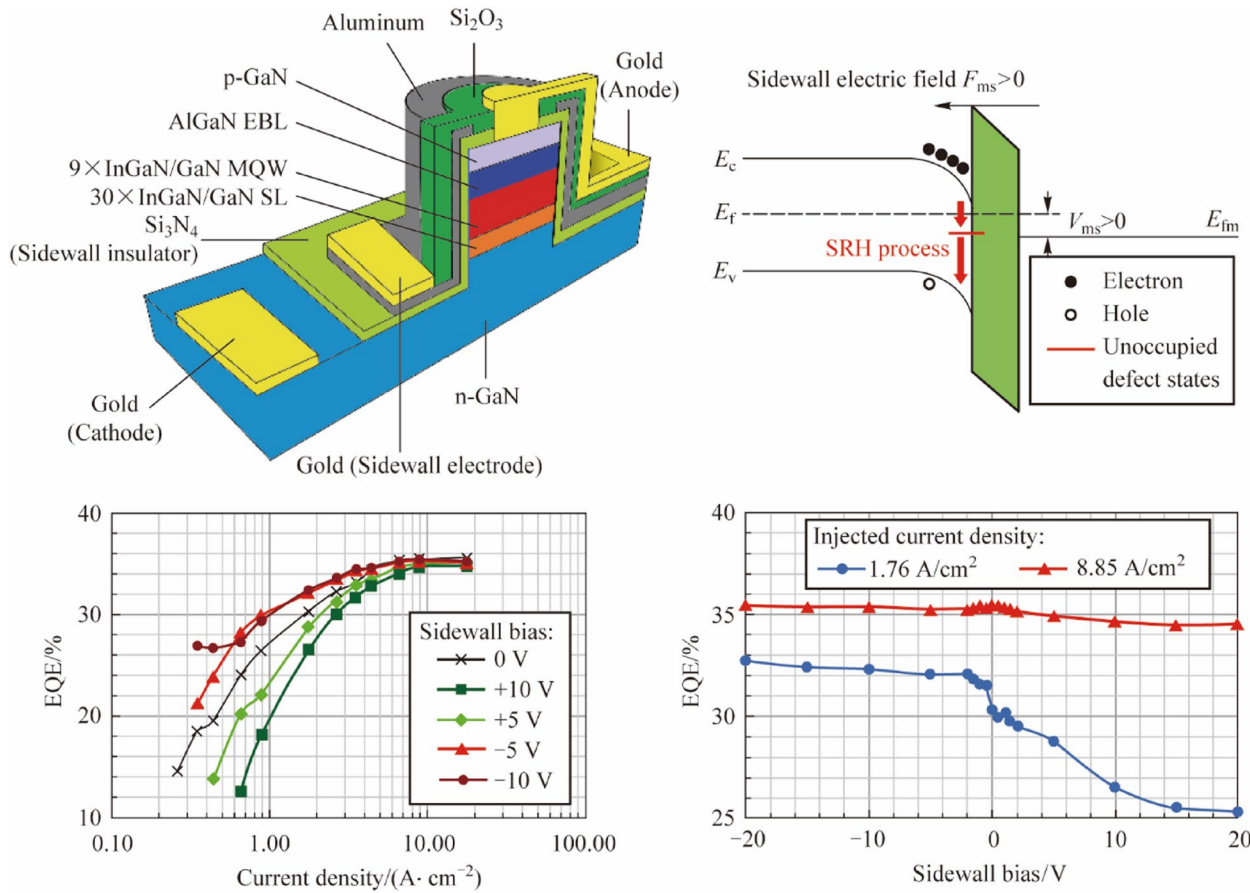
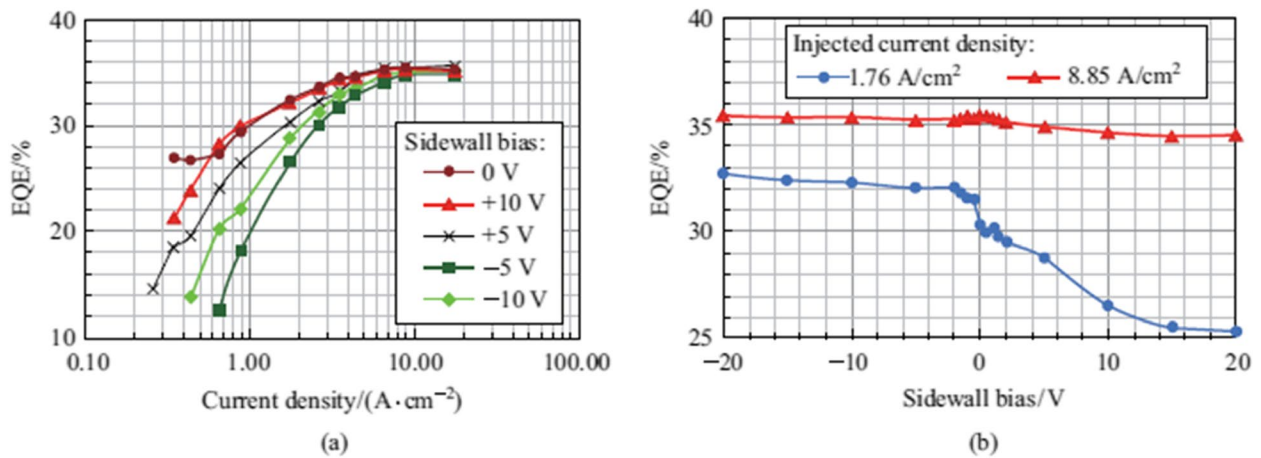
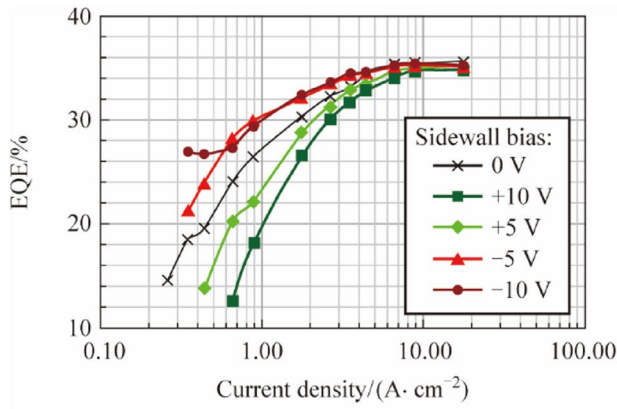


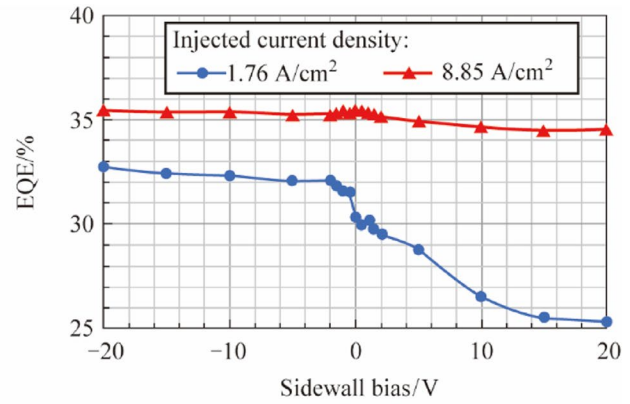
Figure 2 has been updated from:



To:

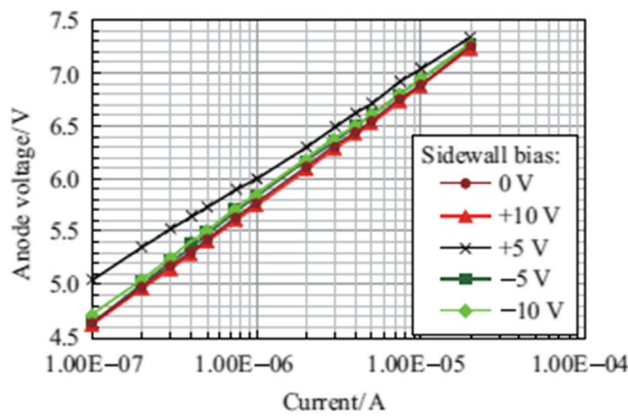


(a)

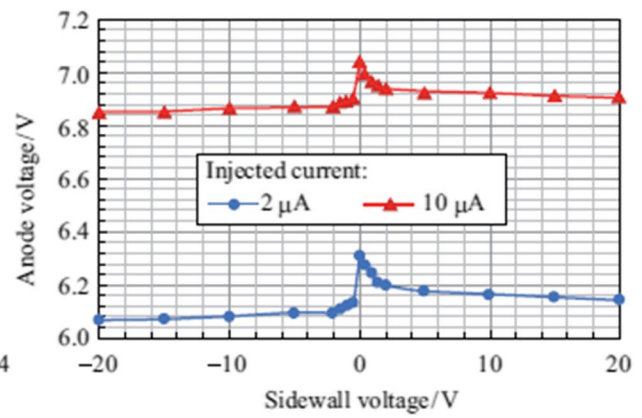


(b)

Figure 3 has been updated from:

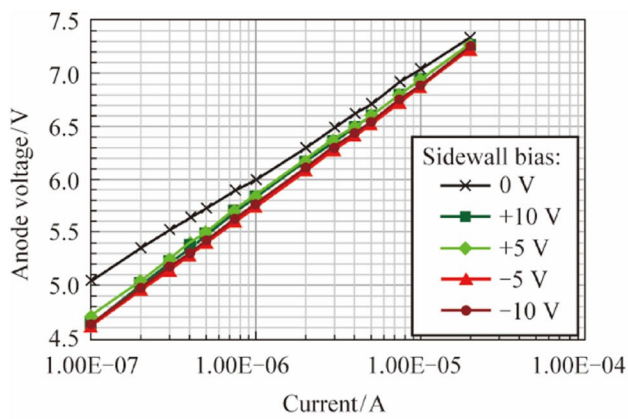


(a)

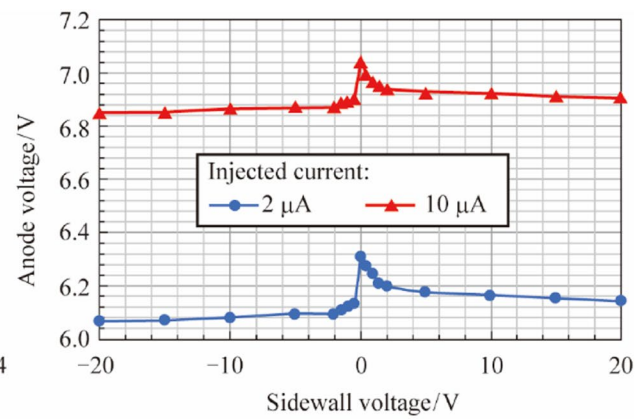


(b)

To:



(a)



(b)

The original article [1] has been updated.

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## Reference

1. Yin, J., Hwang, D., Siboni, H.Z., et al.: Efficiency improvement by using metal–insulator–semiconductor structure in InGaN/GaN micro-light-emitting diodes. *Front. Optoelectron.* **17**, 8 (2024). <https://doi.org/10.1007/s12200-024-00111-9>